

Absolute Maximum Ratings (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	Ic	-200	mA

Thermal Characteristics (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	Pd	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	625	°C/W
Operating and Storage Temperature Range	Tj, T _{STG}	-55 to +150	°C

ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

5. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

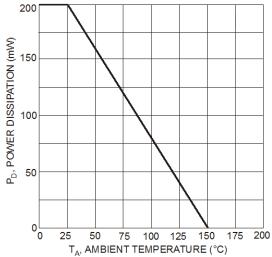


Fig. 1 Max Power Dissipation vs. Ambient Temperature



Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					
Collector-Base Breakdown Voltage	BV _{CBO}	-40	_	V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	-40	_	V	$I_{C} = -1 \text{mA}, I_{B} = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	_	V	$I_E = -10\mu A, I_C = 0$
Collector Cutoff Current	I _{CEX}	_	-50	nA	$V_{CE} = -30V$, $V_{EB(OFF)} = -3V$
Base Cutoff Current	I _{BL}	_	-50	nA	$V_{CE} = -30V$, $V_{EB(OFF)} = -3V$
ON CHARACTERISTICS (Note 7)					
		60	_		$I_{C} = -100\mu A, V_{CE} = -1V$
DC Current Gain		80	_		$I_C = -1mA$, $V_{CE} = -1V$
DC Current Gain	h _{FE}	100 60	300	_	$I_{C} = -10 \text{mA}, V_{CE} = -1 \text{V}$
		30	_		$I_{C} = -50 \text{mA}, V_{CE} = -1 \text{V}$
			0.00		$I_C = -100 \text{mA}, V_{CE} = -1 \text{V}$ $I_C = -10 \text{mA}, I_R = -1 \text{mA}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	-0.20 -0.30	V	, ,
		-0.85		$I_C = -50 \text{mA}, I_B = -5 \text{mA}$ $I_C = -10 \text{mA}, I_B = -1 \text{mA}$	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-0.65	-0.65 -0.95	V	Ic = -10mA, I _B = -1mA Ic = -50mA, I _B = -5mA
SMALL SIGNAL CHARACTERISTICS			0.00		IC = JOHA, IB = JOHA
Output Capacitance	Сово	_	4.5	pF	$V_{CB} = -5V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C _{IBO}	_	10		V _{EB} = -0.5V, f = 1.0MHz, I _C = 0
Input Impedance	h _{IE}	2	12	kΩ	, , , ,
Voltage Feedback Ratio	h _{RE}	0.1	10	x 10 ⁻⁴	$V_{CE} = 1V, I_{C} = 10mA,$
Small Signal Current Gain	HFE	100	400		f = 1kHz
Output Admittance	h _{OE}	3	60	μS	
Current Gain-Bandwidth Product	f _T	300	_	MHz	V _{CE} = -20V, I _C = -10mA, f = 100MHz
Noise Figure	NF	_	4	dB	$V_{CE} = -5V, I_{C} = -100\mu A,$ $R_{S} = 1k\Omega, f = 1kHz$
SWITCHING CHARACTERISTICS	•				
Delay Time	t _d	_	35	ns	$V_{CC} = -3V, I_{C} = -10mA,$
Rise Time	t _r		35	ns	$I_{B1} = -1 \text{mA}, V_{BE(off)} = 0.5 \text{V}$
Storage Time	ts		225	ns	$V_{CC} = -3V, I_{C} = -10mA,$
Fall Time	t _f		75	ns	$I_{B1} = I_{B2} = -1mA$

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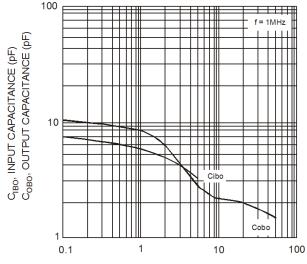
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7. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%. Note:

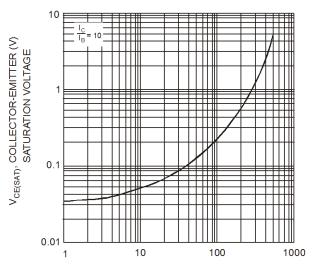
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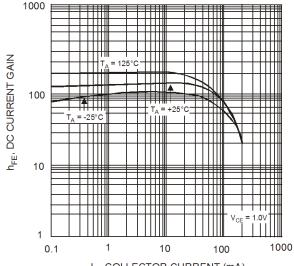
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



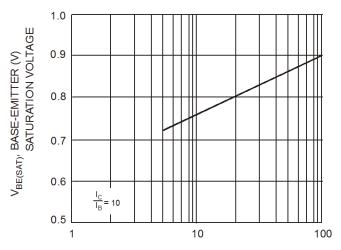
V_{CB}, COLLECTOR-BASE VOLTAGE (V) Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage



I_C, COLLECTOR CURRENT (mA)
Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current



I_C, COLLECTOR CURRENT (mA) Fig. 3, Typical DC Current Gain vs Collector Current

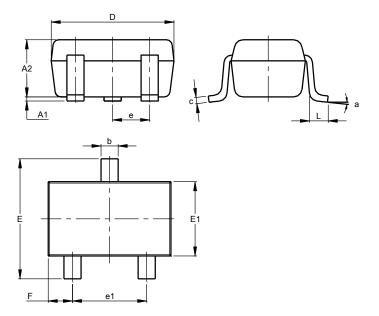


I_C, COLLECTOR CURRENT (mA) Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current



Package Outline Dimensions

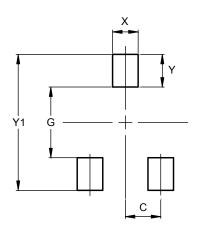
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SOT323					
Dim	Min	Max	Тур		
A1	0.00	0.10	0.05		
A2	0.90	1.00	0.95		
b	0.25	0.40	0.30		
C	0.10	0.18	0.11		
D	1.80	2.20	2.15		
Е	2.00	2.20	2.10		
E1	1.15	1.35	1.30		
е	0.650 BSC				
e1	1.20	1.40	1.30		
F	0.375	0.475	0.425		
ш	0.25	0.40	0.30		
а	0°	8°			
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value		
פווטופווזטווט	(in mm)		
С	0.650		
G	1.300		
Х	0.470		
Υ	0.600		
Y1	2.500		

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